

FEATURES

• Medium Power Complementary Silicon Transistors

1.BASE

2.COLLECTOR

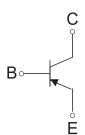
3.EMITTER



TO-220

MAXIMUM RATINGS (Ta=25 unless otherwise noted)

Symbol	Parameter	TIP42A TIP42B TIP42C		TIP42C	Unit
V _{CBO}	Collector-Base Voltage	-60 -80 -100			V
V _{CEO}	Collector-Emitter Voltage	-60	-80	-100	V
V _{EBO}	Emitter-Base Voltage	-5			V
Ic	Collector Current -Continuous	-6			Α
Pc	Collector Power Dissipation	2			W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55to+150			°C

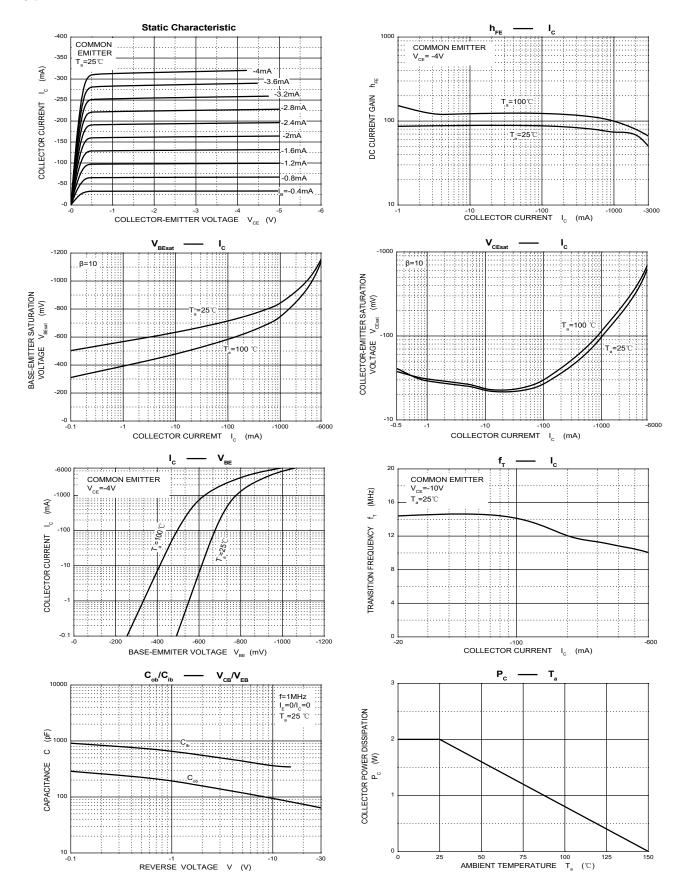


ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Max	Unit
1	TIP42 TIP42A TIP42B TIP42C	$V_{(BR)CBO}$	I _C = -1mA, I _E =0	-40 -60 -80 -100		V
1	TIP42 TIP42A TIP42B TIP42C	V _{(BR)CEO} *	I _C = -30mA, I _B =0	-40 -60 -80 -100		V
Emitter-base breakdown voltage		$V_{(BR)EBO}$	I _E = -1mA, I _C =0	-5		V
1 1	TIP42 TIP42A TIP42B TIP42C	І _{сво}	V_{CB} =-40V, I_{E} =0 V_{CB} =-60V, I_{E} =0 V_{CB} =-80V, I_{E} =0 V_{CB} =-100V, I_{E} =0		-0.4	mA
	42/42A 2B/42C	I _{CEO}	V _{CE} = -30V, I _B = 0 V _{CE} = -60V, I _B = 0		-0.7	mA
Emitter cut-off current		I_{EBO}	V _{EB} =-5V, I _C =0		-1	mA
DC current cain		h _{FE(1)}	V_{CE} =-4V, I_{C} =-0.3A	30		
DC current gain		h _{FE(2)}	N _{FE(2)} V _{CE} =-4 V, I _C = -3A		75	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I _C =-6A, I _B =-0.6A		-1.5	V
Base-emitter voltage		V_{BE}	V _{CE} =-4V, I _C =-6A		-2	V
Transition frequency		f_T	V _{CE} =-10V,I _C =-0.5	3		MHz

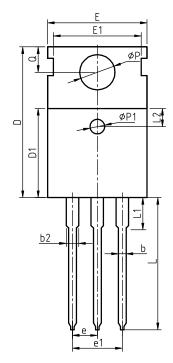
*Pulse test

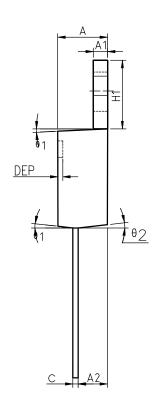
Typical Characteristics



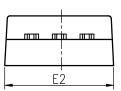


Package Information TO-220





COMMON DIMENSIONS



SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
Α	4.40	4.57	4.70	0.173	0.180	0.185
A1	1. 27	1.30	1.33	0.050	0.051	0.052
A2	2. 35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1. 17	1. 27	1.36	0.046	0.050	0.054
С	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9. 10	9. 20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0. 386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
е		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0. 252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
Р	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ 1	5°	7°	9°	5°	7°	9°
θ2	1°	3°	5°	1°	3°	5°
θ 3	1°	3°	5°	1°	3°	5°



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